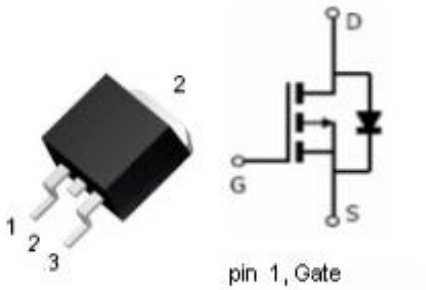
isc P-Channel MOSFET Transistor IRF9Z34NS

·FEATURES

- Static drain-source on-resistance:
  $R_{DS(on)} \leqslant 100m\Omega$(@$V_{GS}$= -10V; I_D= -10A)
- Advanced trench process technology
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

- Fast switching application.



D2PAK

pin 1, Gate
2, Drain
3, Source

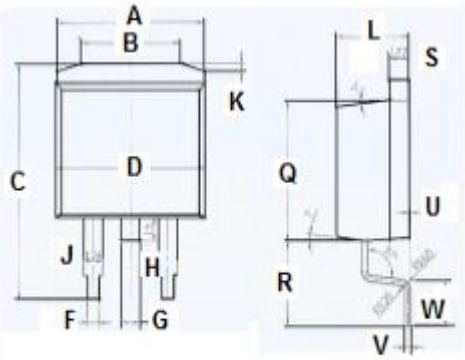
TO-263 Package

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-55	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	-19	A
P_D	Total Dissipation @T_C=25℃	68	W
T_j	Max. Operating Junction Temperature	-55~175	℃
T_{stg}	Storage Temperature	-55~175	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	2.2	℃/W



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

isc P-Channel MOSFET Transistor IRF9Z34NS

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= -250 μA	-55		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D= -250 μA	-2	-4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= -10V; I_D= -10A		100	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V; V_{DS}= 0V		±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= -55V; V_{GS}= 0V		-25	μA
V_{SD}	Diode forward voltage	I_s= -10A, V_{GS} = 0V		1.6	V